GPT13N50C / GPT13N50CD

POWER FIELD EFFECT TRANSISTOR

GENERAL DESCRIPTION

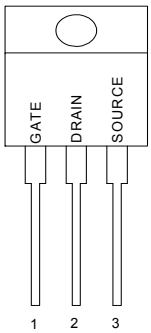
This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

FEATURES

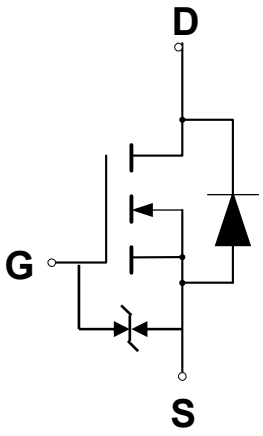
- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and V_{DS}(on) Specified at Elevated Temperature
- Ciss improvement

PIN CONFIGURATION

TO220/TO-220F
Top View



SYMBOL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current — Continuous	I_D	13	A
— Pulsed	I_{DM}	39	
Gate-to-Source Voltage — Continue	V_{GS}	±30	V
Total Power Dissipation – TO220	P_D	193	W
– TO220FP		47	
Derate above 25℃ – TO220		1.54	W/℃
– TO220FP		0.38	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	℃
Single Pulse Drain-to-Source Avalanche Energy — T_J = 25℃ (V_{DD} = 100V, V_{GS} = 10V, I_L = 11A, L = 10mH, R_G = 25Ω)	E_{AS}	605	mJ
Thermal Resistance — Junction to Case -TO220	θ_{JC}	0.64	℃/W
— Junction to Case -TO220FP		3.7	
— Junction to Ambient -TO220, TO220FP	θ_{JA}	62.5	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	℃
ESD SENSITIVITY — HBM, C=100pF, R=1.5kΩ	Vesd	2000	V

ORDERING INFORMATION

Part Number	Package
GPT13N50CGN220*	TO-220
GPT13N50CDGN220FP*	TO-220F

***Note:** G : Suffix for PB Free Product

ELECTRICAL CHARACTERISTICS

Unless otherwise specified, T_J = 25℃.

			GPT13N50C			
Characteristic		**Symbol**	**Min**	**Typ**	**Max**	**Units**
Drain-Source Breakdown Voltage (V_{GS} = 0 V, I_D = 250 μA)		$V_{(BR)DSS}$	500			V
Drain-Source Leakage Current (V_{DS} = 500 V, V_{GS} = 0 V) (V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125℃)		I_{DSS}			1 10	μA
Gate-Source Leakage Current-Forward (V_{gsf} = 30 V, V_{DS} = 0 V)		I_{GSSF}			100	nA
Gate-Source Leakage Current-Reverse (V_{gsr} = -30 V, V_{DS} = 0 V)		I_{GSSR}			100	nA
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	3.2		5.2	V
Static Drain-Source On-Resistance (V_{GS} = 10 V, I_D = 6.5A) *		$R_{DS(on)}$			0.49	Ω
Forward Transconductance (V_{DS} = 15 V, I_D = 6.5A) *		g_{FS}		8.7		S
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}		1578		pF
Output Capacitance		C_{oss}		180		pF
Reverse Transfer Capacitance		C_{rss}		9.8		pF
Turn-On Delay Time	(V_{DD} = 250 V, I_D = 13 A, R_G = 25Ω) *	$t_{d(on)}$		33		ns
Rise Time		t_r		59		ns
Turn-Off Delay Time		$t_{d(off)}$		75		ns
Fall Time		t_f		34.8		ns
Total Gate Charge	(V_{DS} = 400 V, I_D = 13 A, V_{GS} = 10 V)*	Q_g		31		nC
Gate-Source Charge		Q_{gs}		8.7		nC
Gate-Drain Charge		Q_{gd}		12		nC
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage(1)	(I_S =13 A, V_{GS} = 0 V, dI_S/d_t = 100A/μs)	V_{SD}			1.5	V
Forward Turn-On Time		t_{on}		**		ns
Reverse Recovery Time		t_{rr}		450		ns

* Pulse Test: Pulse Width ≦300μs, Duty Cycle ≦2%

** Negligible, Dominated by circuit inductance

TYPICAL ELECTRICAL CHARACTERISTICS

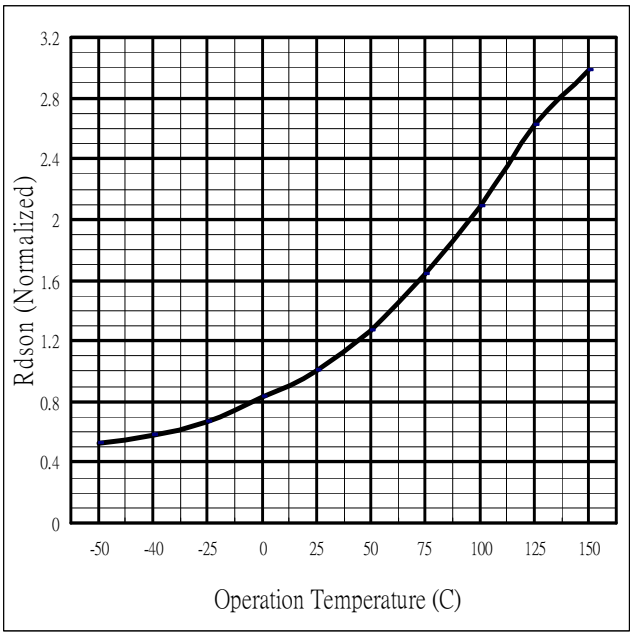


Fig 1. On-Resistance Variation with vs. Temperature

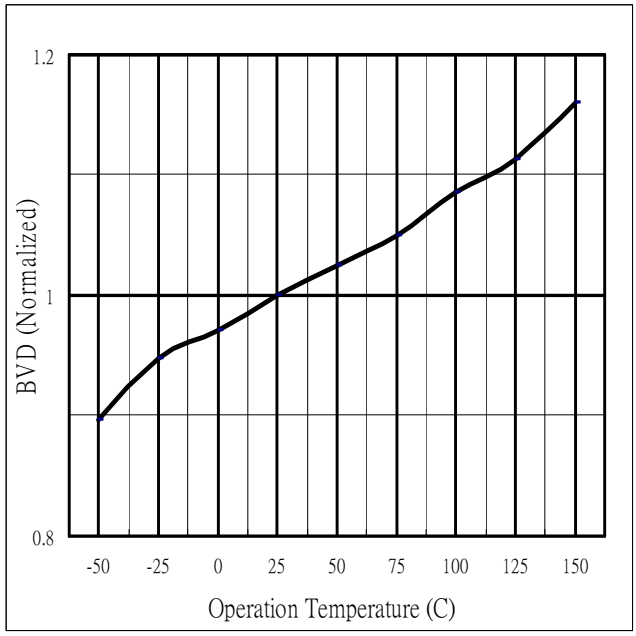


Fig.2 Breakdown Voltage Variation vs. Temperature

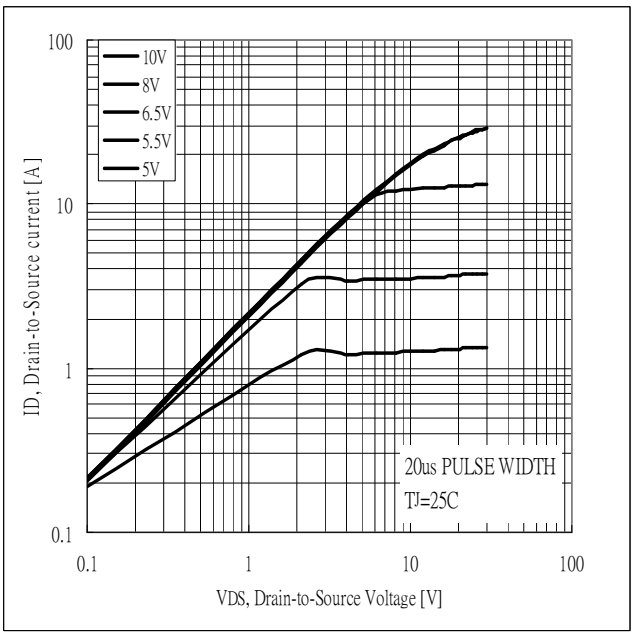


Fig 3. Typical Output Characteristics

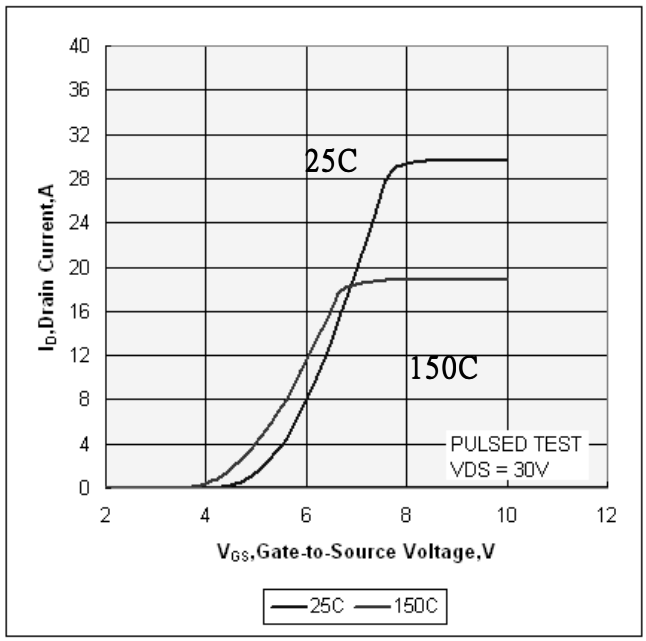


Fig 5. Typical Transfer Characteristics

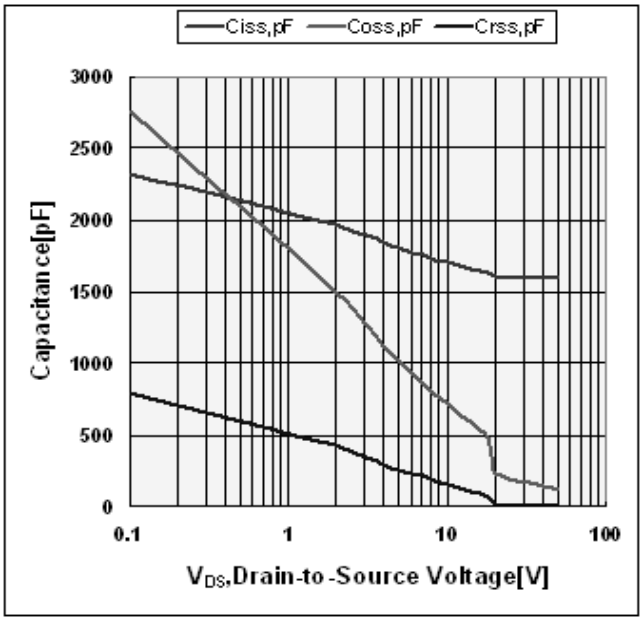


Fig 6. Typical Capacitance Vs. Gate-to-Source Voltage

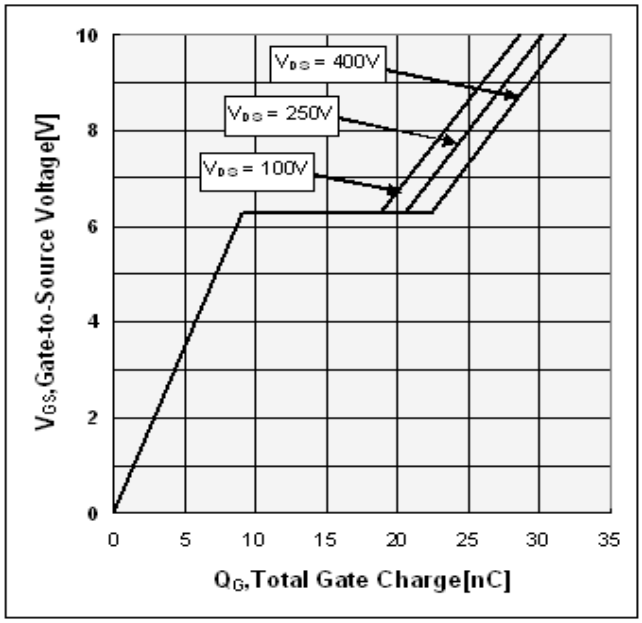
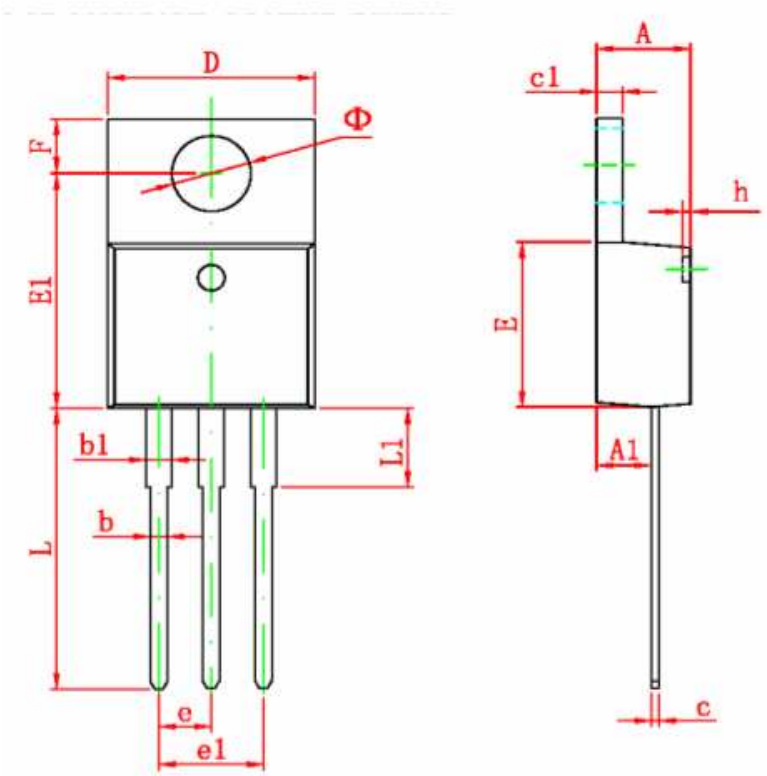


Fig 6. Typical Gate Charge Vs. Drain-to-Source Voltage

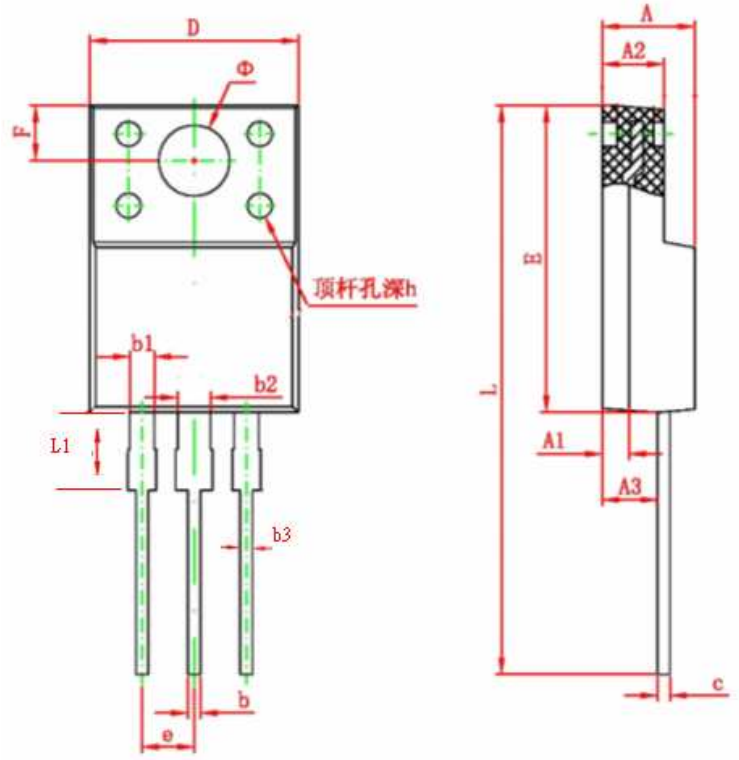
PACKAGE DIMENSION

TO-220



Symbol	Dimensions In Millimeters	
	Min.	Max
A	4.40	4.80
A1	2.10	2.84
b	0.71	0.91
b1	1.17	1.37
c	0.30	0.60
c1	1.17	1.47
D	9.40	10.60
E	8.40	9.60
e	2.54 TYP.	
e1	4.90	5.60
F	3.00 REF.	
Φ	3.50 REF.	
h	0.00	0.30
L	12.50	14.00
L1	3.50	4.00

TO-220F



Symbol	Dimensions In Millimeters	
	Min.	Max
A	3.80	4.70
A1	1.3 REF.	
A2	2.20	3.20
A3	2.10	3.20
b	0.30	0.95
b1	1.00	1.75
b2	1.00	1.75
b3	0.50	0.80
c	0.30	0.90
D	9.90	10.40
E	14.60	16.20
e	2.54 TYP.	
F	3.00 REF.	
Φ	3.50 REF.	
h	0.00	0.30
L	28.00	30.00
L1	3.20	3.55

IMPORTANT NOTICE

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